

# LINEAR INTEGRATED CIRCUITS

7929225 S G S SEMICONDUCTOR CORP



## PRELIMINARY DATA

### DUAL OPERATIONAL AMPLIFIERS

- INTERNALLY COMPENSATED
- SHORT-CIRCUIT PROTECTED
- LOW POWER CONSUMPTION
- WIDE COMMON-MODE AND DIFFERENTIAL VOLTAGE RANGES
- NO LATCH-UP

The MC 1458 is a dual operational amplifier with frequency and phase compensation built into the chip, available in 8-lead minidip package and in 8-lead micropackage. It is intended for a wide range of applications where space and cost saving are the main goals. In spite of that, the MC 1458 offers good performance and absence of latch-up makes the device ideal for use as voltage follower, integrator, summing amplifier and general feedback applications.

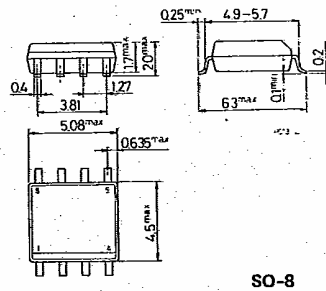
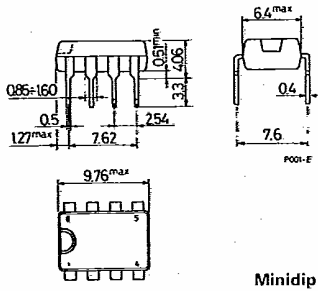
### ABSOLUTE MAXIMUM RATINGS

$V_s$	Supply voltage		$\pm 18$	V
$V_i$	Input voltage (*)		$\pm 15$	V
$V_{iD}$	Differential input voltage		$\pm 30$	V
$P_{tot}$	Power dissipation at $T_{amb} = 70^\circ\text{C}$	Minidip	665	mW
		Micropackage	400	mW
$T_{op}$	Operating temperature		0 to 70	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55 to 150	$^\circ\text{C}$

(\*) For  $V_s$  lower than  $\pm 15\text{V}$ , the absolute maximum input voltage is equal to the supply voltage.

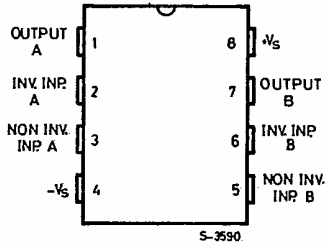
### MECHANICAL DATA

Dimensions in mm



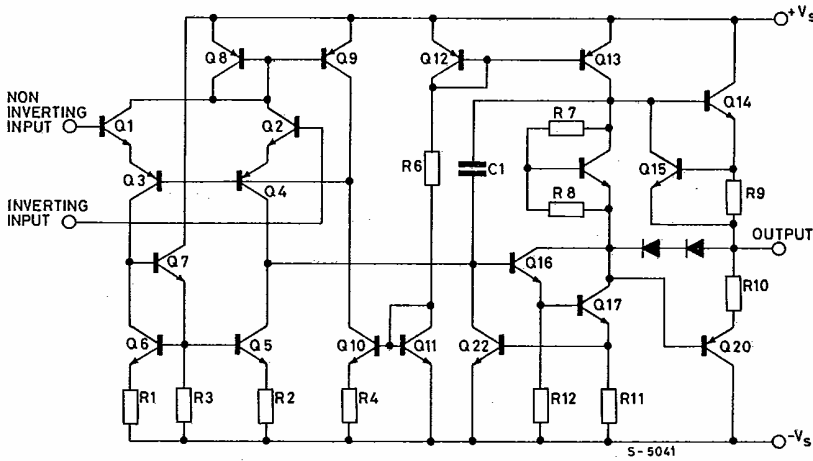


**CONNECTION DIAGRAM AND ORDERING NUMBERS**  
(top view)



Type	Minidip	SO-8
MC 1458	MC 1458 P1	MC 1458 M
MC 1458C	MC 1458 CP1	MC 1458 CM

**SCHEMATIC DIAGRAM (one section)**



**THERMAL DATA**

		Minidip	SO-8
$R_{th\ J-amb}$	Thermal resistance junction-ambient	max - 120 °C/W	200* °C/W

\* Measured with the device mounted on a ceramic substrate (25 x 16 x 0.6 mm.).



**ELECTRICAL CHARACTERISTICS** ( $V_s = \pm 15V$ ,  $T_{amb} = 25^\circ C$ , unless otherwise specified)

Parameter	Test conditions	MC 1458			MC 1458C			Unit		
		Min.	Typ.	Max.	Min.	Typ.	Max.			
$I_s$	Supply current (both amplifiers)			5.6			8	mA		
$I_b$	Input bias current			0.5			0.7	$\mu A$		
		$0^\circ C < T_{op} < 70^\circ C$			0.8				1	
$V_{os}$	Input offset voltage	$R_g \leq 10 K\Omega$	2	6		2	10	mV		
		$R_g \leq 10 K\Omega$ $0^\circ C < T_{op} < 70^\circ C$			7.5				12	
$\frac{\Delta V_{os}}{\Delta T}$	Input offset voltage drift	$R_g = 10 K\Omega$ $0^\circ C < T_{op} < 70^\circ C$	6			6		$\mu V/^\circ C$		
$I_{os}$	Input offset current		20	200		20	300	nA		
		$0^\circ C < T_{op} < 70^\circ C$			300				400	
$\frac{\Delta I_{os}}{\Delta T}$	Input offset current drift	$0^\circ C < T_{op} < 70^\circ C$	0.5			0.5		nA/°C		
$I_{sc}$	Output short circuit current		20			20		mA		
$G_v$	Large signal open loop voltage gain	$R_L = 2K\Omega$	$T_{amb} = 0 \text{ to } 70^\circ C$		83				dB	
					86	106				
		$R_L = 10K\Omega$	$T_{amb} = 0 \text{ to } 70^\circ C$				83			dB
							86	106		
$B$	Unity gain bandwidth		0.8			0.8		MHz		
$e_N$	Input noise voltage	$B = 10\text{Hz to } 10\text{KHz}$	$R_g = 1 K\Omega$	3		3		$\mu V$		
			$R_g = 500 K\Omega$	25		25				
$V_o$	Output voltage swing	$R_L = 2 K\Omega$	$\pm 10$	$\pm 13$		$\pm 9$	$\pm 13$	V		
		$R_L = 10 K\Omega$	$\pm 12$	$\pm 14$		$\pm 11$	$\pm 14$			
$SR$	Slew Rate		0.3			0.3		V/ $\mu s$		
$CMR$	Common mode rejection		70	90		60	90	dB		
$SVR$	Supply voltage rejection		76	90		90		dB		
	Common mode input voltage range		$\pm 12$	$\pm 13$		$\pm 11$	$\pm 13$	V		